

ABSTRACT OF THE DISCLOSURE

The present invention provides an ultrathin thin film integrated circuit and a thin film integrated circuit device including the thin film integrated circuit device.

5 Accordingly, the design of a product is not spoilt while an integrated circuit formed from a silicon wafer, which is thick and produces irregularities on the surface of the product container. The thin film integrated circuit according to the present invention includes a semiconductor film as an active region (for example a channel region in a thin film transistor), unlike an integrated circuit formed from a conventional silicon wafer. The

10 thin film integrated circuit according to the present invention is thin enough that the design is not spoilt even when a product such as a card or a container is equipped with the thin film integrated circuit.